What is claimed is:

112s ! "[ ]" notation forbidden .

[c1] A method for fabricating an integrated optical isolator, comprising:

depositing a wire grid material on a magneto-optical substrate;

depositing a resist film on the wire grid material;

bringing a mold with a wire grid pattern in contact with the resist film and compressing the mold and resist film together so as to emboss the wire grid pattern in the resist film; and

transferring the wire grid pattern in the resist film to the wire grid material on the magneto-optical substrate by etching.

[c2] The method of claim **1**, wherein the wire grid material comprises a metallic material.

[c3] The method of claim **1**, wherein the wire grid material comprises a dielectric material sandwiched between two metallic materials.

[c4] The method of claim **3**, wherein the metallic materials are selected from the group consisting of Al, Au, Cu, Ir, Mo, Ni, Os, Pt, Rh, and W.

[c5] The method of claim **3**, wherein the dielectric material is selected from the group consisting of Si, SiO_2, and GaAs.

[c6] The method of claim **1**, wherein the resist film comprises a thermoplastic polymer.

[c7] The method of claim **6**, further comprising heating the mold and the resist film to a temperature above the glass transition temperature of the thermoplastic polymer prior to bringing the mold in contact with the resist film.

[c8] The method of claim 1, further comprising coating the magneto-optical substrate with an anti-reflective material prior to depositing the wire grid material on the substrate.

[c9] A method for fabricating a wire grid polarizer, comprising:

depositing a wire grid material on a substrate, wherein the wire grid material comprises a dielectric material sandwiched between two metallic materials;

depositing a resist film on the wire grid material;

bringing a mold with a wire grid pattern in contact with the resist film and compressing the mold and resist film together so as to emboss the wire grid pattern in the resist film; and

transferring the wire grid pattern in the resist film to the wire grid material on the substrate by etching.

[c10] The method of claim **9**, wherein the metallic materials are selected from the group consisting of Al, Au, Cu, Ir, Mo, Ni, Os, Pt, Rh, and W.

[c11] The method of claim **9**, wherein the dielectric material is selected from the group of Si, SiO_2, and GaAs.

[c12] The method of claim **9**, wherein the resist film comprises a thermoplastic polymer.

[c13] The method of claim **12**, further comprising heating the mold, the resist film and the substrate to a temperature above the glass transition temperature of the thermoplastic polymer prior to contacting the mold with the resist film.

[c14] The method of claim **9**, further comprising applying an anti-reflective coating on the substrate prior to depositing the wire grid material on the substrate.

[c15] The method of claim **9**, wherein the substrate is made of a magneto-optical material

[c16] An integrated optical isolator, comprising:

a magneto-optical substrate having a first surface and a second surface, the first and second surfaces being coated with an anti-reflection material;

a first wire grid structure formed on the first surface, the first wire grid structure being adapted to suppress reflection of rejected polarization; and

a second wire grid structure formed on the second surface and rotated an angle with respect to the first wire grid structure.

[c17] The integrated optical isolator of claim **16**, wherein the first wire grid structure comprises a plurality of substantially parallel grid elements, each grid element comprising a dielectric material sandwiched between two metallic materials.

[c18] The integrated optical isolator of claim **17**, wherein the metallic materials are selected from the group consisting of Al, Au, Cu, Ir, Mo, Ni, Os, Pt, Rh, and W.

[c19] The integrated optical isolator of claim **17**, wherein the dielectric material is selected from the group of Si, SiO_2, and GaAs.

[c20] A wire grid polarizer, comprising:
a substrate which is transparent at a selected wavelength; and
an anti-reflective wire grid structure formed on a surface of the substrate.

[c21] The wire grid polarizer of claim **20**, wherein the surface of the substrate on which the anti-reflective wire grid structure is formed is coated with an anti-reflective material.

[c22] The wire grid polarizer of claim **20**, wherein the anti-reflective wire grid structure comprises a plurality of substantially parallel grid elements, each grid element comprising a dielectric material sandwiched between two metallic materials.

[c23] The wire grid polarizer of claim **22**, wherein the metallic materials are selected from the group consisting of Al, Au, Cu, Ir, Mo, Ni, Os, Pt, Rh, and W.

[c24] The wire grid polarizer of claim **22**, wherein the dielectric material is selected from the group of Si, SiO_2, and GaAs.